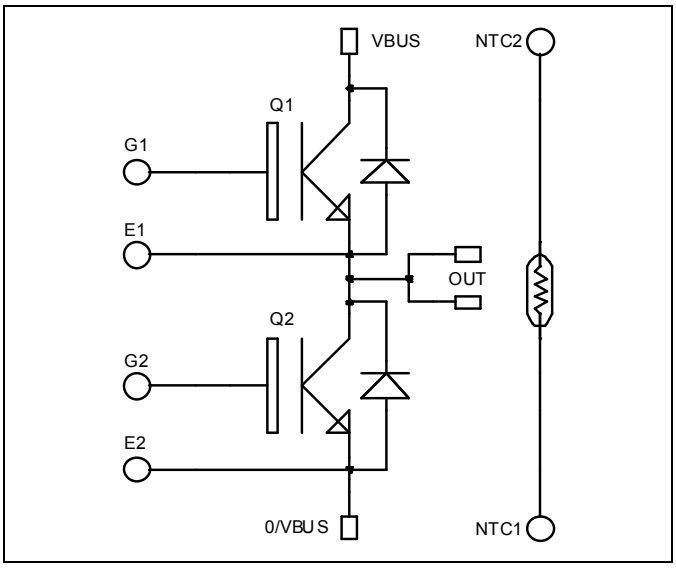
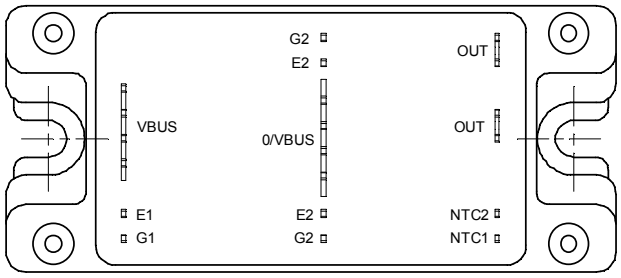
APTGF100A120T

Phase leg
NPT IGBT Power Module

V_{CES} = 1200V
I_C = 100A @ Tc = 80°C





Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Non Punch Through (NPT) FAST IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - Avalanche energy rated
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Easy paralleling due to positive TC of VCEsat
- Low profile

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_C	Continuous Collector Current	T_c = 25°C	150	A
		T_c = 80°C	100	
I_{CM}	Pulsed Collector Current	T_c = 25°C	300	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_c = 25°C	568	W
RBSOA	Reverse Bias Safe Operating Area	T_j = 150°C	300A @ 1200V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed.

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
BV_{CES}	Collector - Emitter Breakdown Voltage	V_{GE} = 0V, I_C = 750 µA		1200			V
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V V_{CE} = 1200V	T_j = 25°C			750	µA
			T_j = 125°C			3750	
$V_{CE(on)}$	Collector Emitter on Voltage	V_{GE} =15V I_C = 100A	T_j = 25°C		3.2	3.7	V
			T_j = 125°C		4.0		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE}, I_C = 2 mA		4.5		6.5	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = ±20 V, V_{CE} = 0V				150	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*	*Min*	*Typ*	*Max*	*Unit*
C_{ies}	Input Capacitance	V_{GE} = 0V V_{CE} = 25V f = 1MHz		6900		pF
C_{oes}	Output Capacitance			660		
C_{res}	Reverse Transfer Capacitance			440		
Q_g	Total gate Charge	V_{GS} = 15V V_{Bus} = 600V I_C = 100A		660		nC
Q_{ge}	Gate – Emitter Charge			70		
Q_{gc}	Gate – Collector Charge			400		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = 15V V_{Bus} = 600V I_C = 100A R_G = 2.5 Ω		35		ns
T_r	Rise Time			65		
$T_{d(off)}$	Turn-off Delay Time			320		
T_f	Fall Time			30		
E_{on}	Turn-on Switching Energy ❶			10.8		mJ
E_{off}	Turn-off Switching Energy ❷			4.6		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = 15V V_{Bus} = 600V I_C = 100A R_G = 2.5 Ω		35		ns
T_r	Rise Time			65		
$T_{d(off)}$	Turn-off Delay Time			360		
T_f	Fall Time			40		
E_{on}	Turn-on Switching Energy ❶			13.9		mJ
E_{off}	Turn-off Switching Energy ❷			6.1		

Reverse diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle	Tc = 70°C		120		A
V_F	Diode Forward Voltage	I_F = 120A			2.0	2.5	V
		I_F = 240A			2.3		
		I_F = 120A	T_j = 125°C		1.8		
t_{rr}	Reverse Recovery Time	I_F = 120A V_R = 800V di/dt =800A/µs	T_j = 25°C		370		ns
			T_j = 125°C		500		
Q_{rr}	Reverse Recovery Charge	I_F = 120A V_R = 800V di/dt =800A/µs	T_j = 25°C		2.64		µC
			T_j = 125°C		13.8		

❶ E_{on} includes diode reverse recovery
❷ In accordance with JEDEC standard JESD24-1

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case		IGBT			0.22	°C/W
			Diode			0.32	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M5			4.7	N.m
Wt	Package Weight					160	g

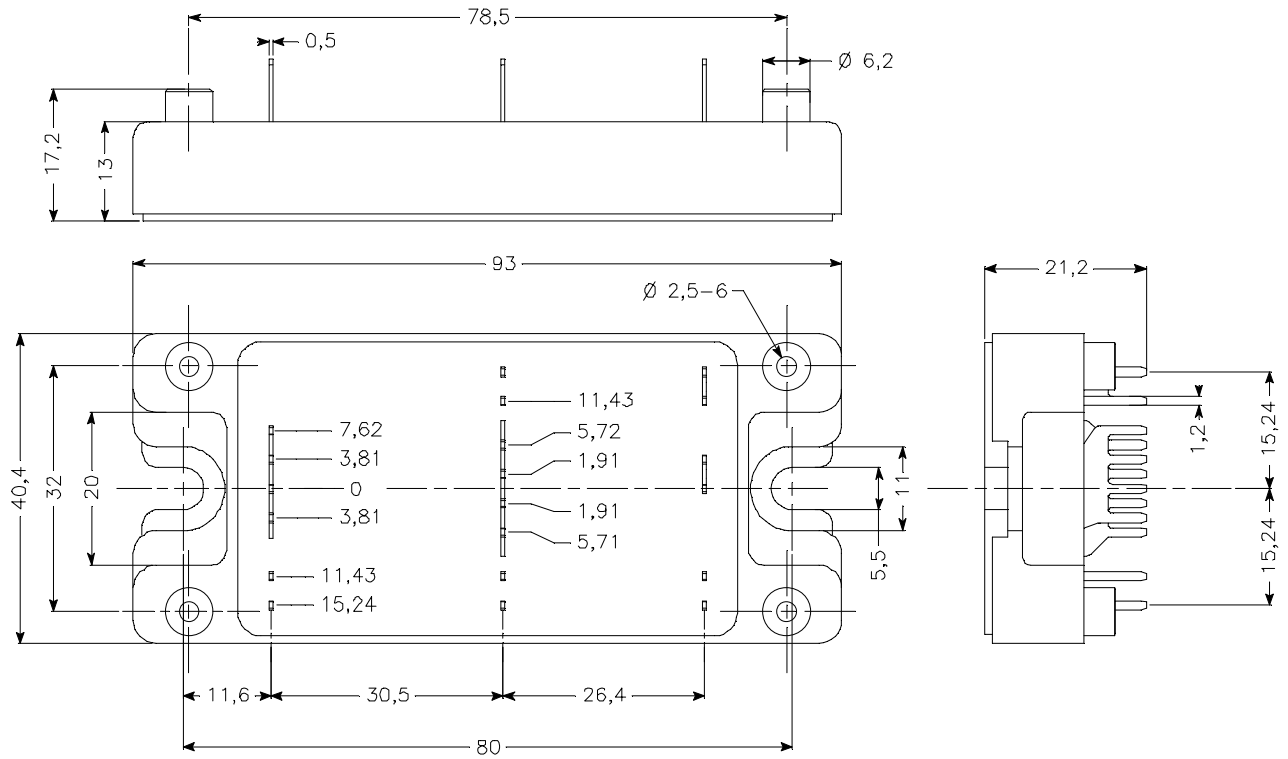
Temperature sensor NTC

Symbol	Characteristic	Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C		68		kΩ
$B_{25/85}$	T_{25} = 298.16 K		4080		K

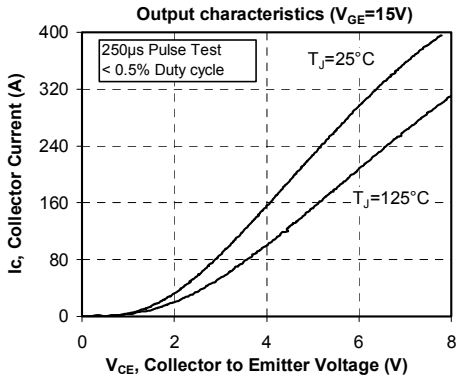
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

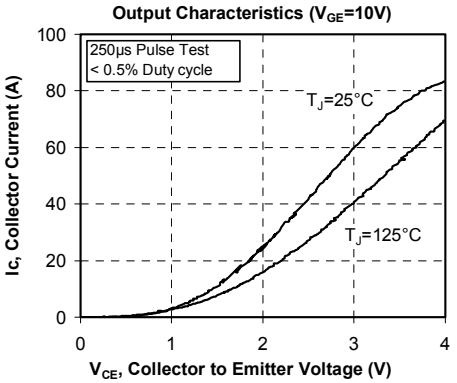
T: Thermistor temperature
R_T: Thermistor value at T

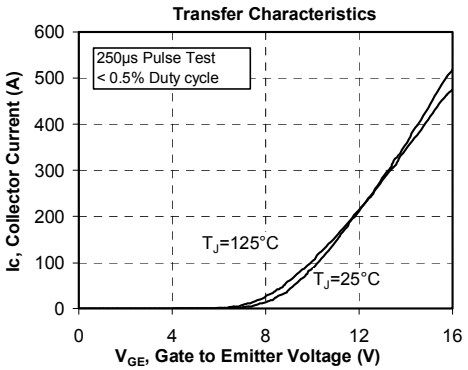
Package outline

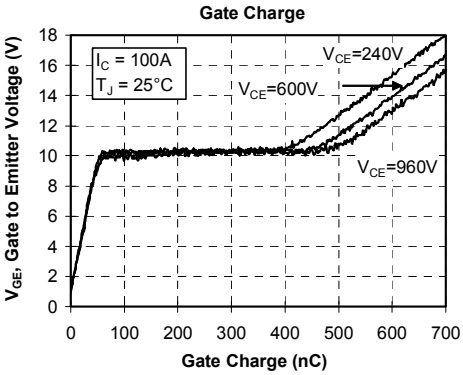


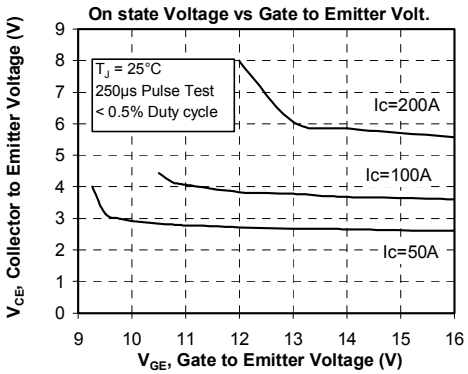
Typical Performance Curve

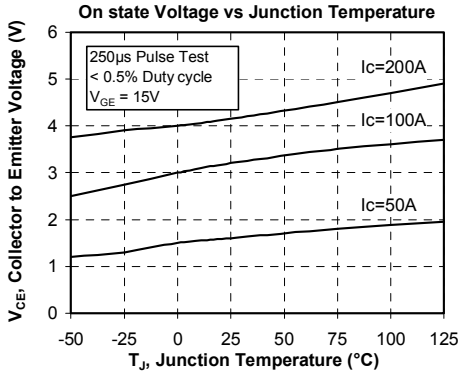


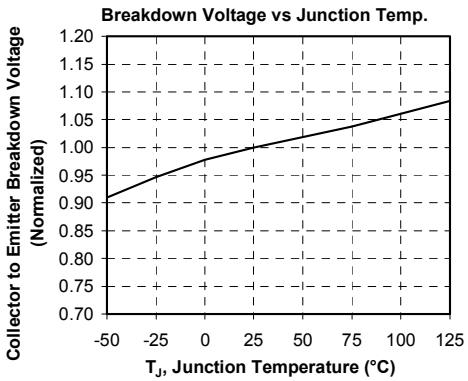


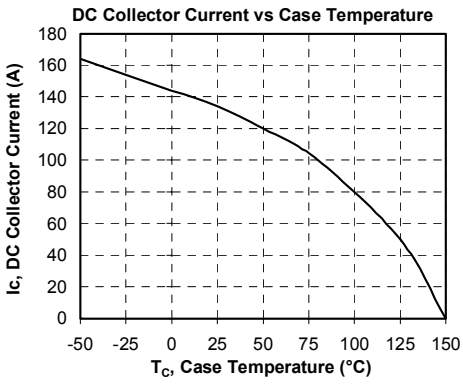




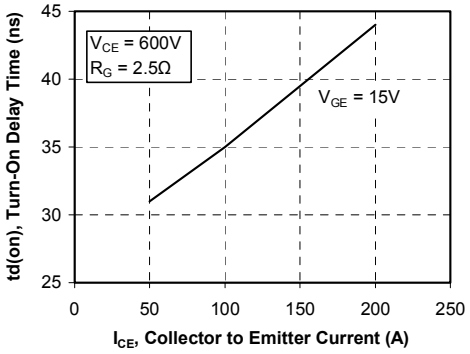




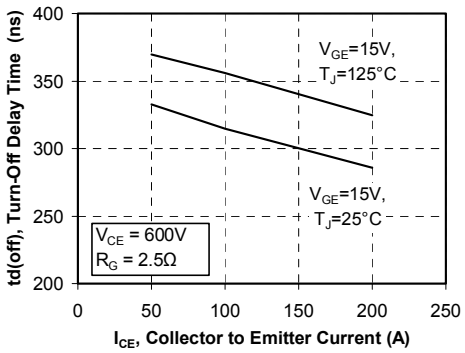




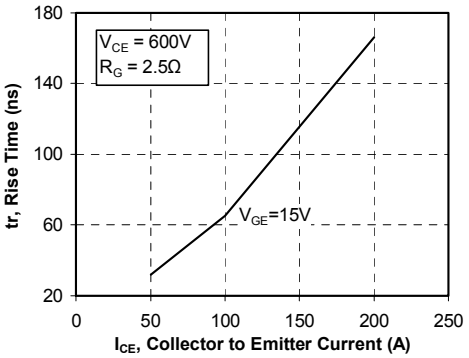
Turn-On Delay Time vs Collector Current



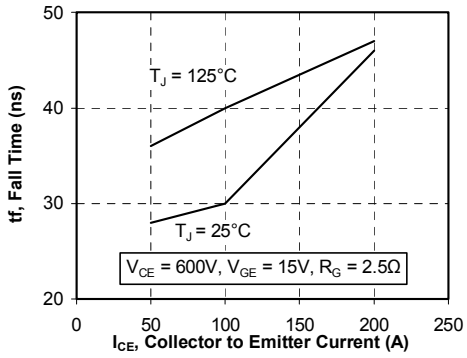
Turn-Off Delay Time vs Collector Current



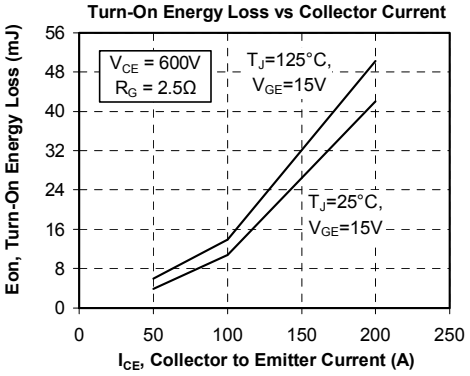
Current Rise Time vs Collector Current



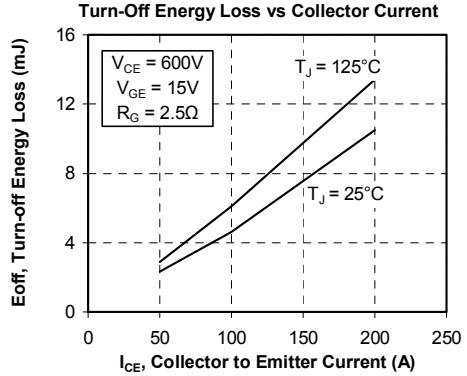
Current Fall Time vs Collector Current



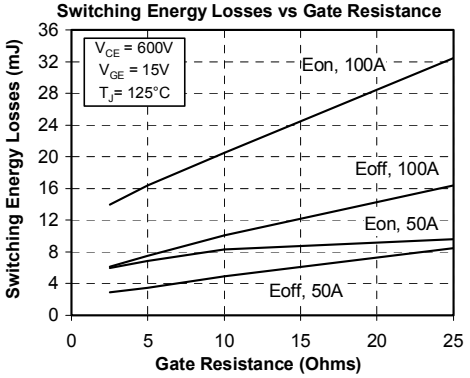
Turn-On Energy Loss vs Collector Current



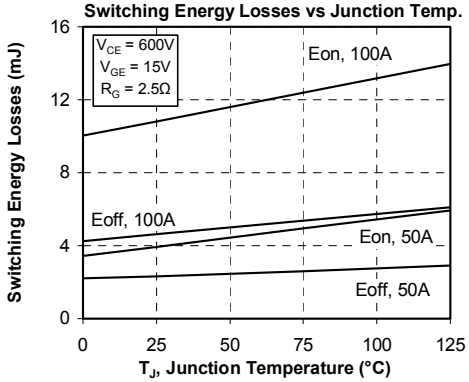
Turn-Off Energy Loss vs Collector Current



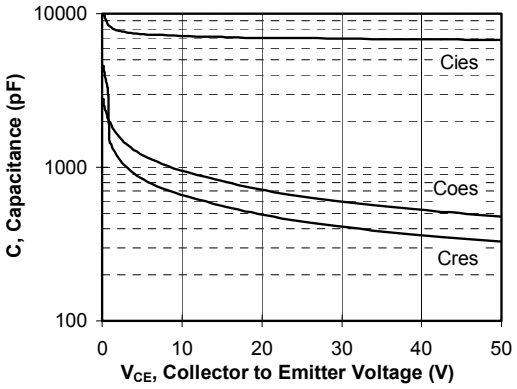
Switching Energy Losses vs Gate Resistance



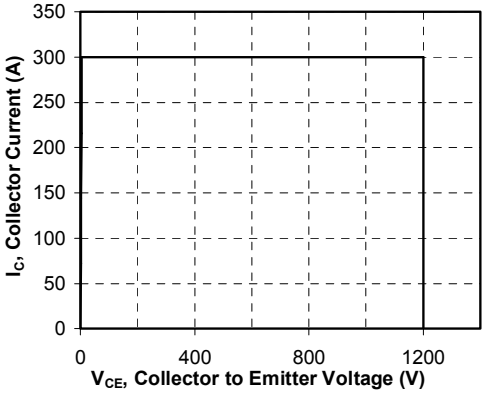
Switching Energy Losses vs Junction Temp.



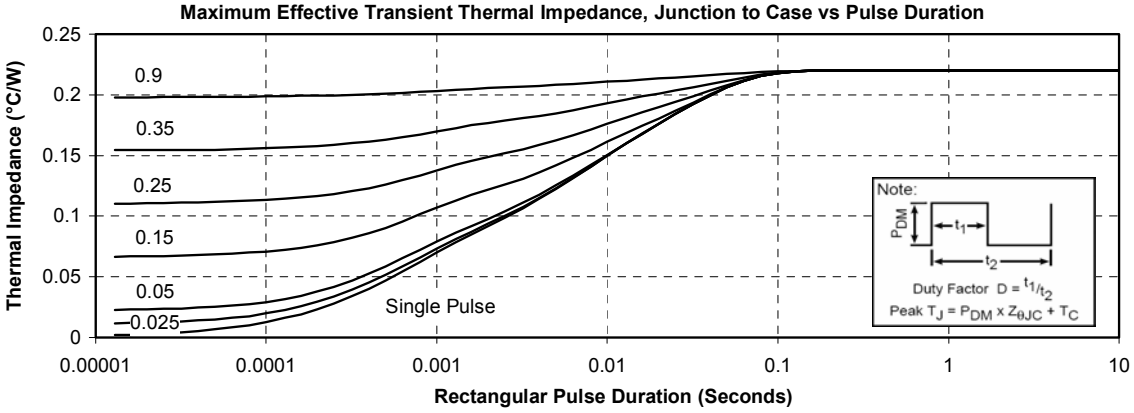
Capacitance vs Collector to Emitter Voltage



Minimum Switching Safe Operating Area



Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



Operating Frequency vs Collector Current